

InGaN Venus Blue LED Chip

ES-CADB V45C

□ Features:

- High radiant flux
- Long operation life
- Lambertian radiation

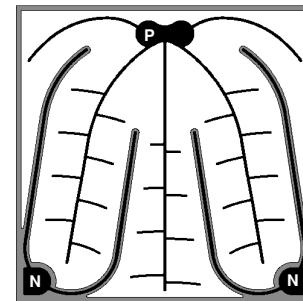
□ Applications:

- Street lighting
- Architectural lighting
- Residential lighting

□ Mechanical Specification:

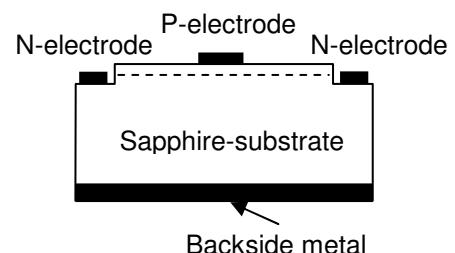
(1) Dimension

Chip size : 45 mil x 45 mil ($1143\pm25\mu\text{m}$ x $1143\pm25\mu\text{m}$)
 Thickness : 5.9 mil ($150 \pm 10 \mu\text{m}$)
 P bonding pad x 2 : 4.4 mil ($112 \pm 10 \mu\text{m}$)
 N bonding pad x 2 : 4.1 mil ($105 \pm 10 \mu\text{m}$)



(2) Metallization

Topside P electrode : Au alloy
 Topside N electrode : Au alloy
 Backside metal : Au alloy



□ Electro-optical Characteristics at 25 °C:⁽¹⁾

Parameter	Symbol		Condition	Min.	Typ.	Max.	Unit
Forward voltage	V_{f1}		$I_f=10\mu\text{A}$	1.6			V
	V_{f2}		$I_f=350\text{mA}$		3.4	3.6	V
Reverse current	I_r		$V_r=5\text{V}$			2.0	μA
Dominant wavelength ⁽²⁾	λ_d		$I_f=350\text{mA}$	445		455	nm
Spectral half-width	$\Delta\lambda$		$I_f=350\text{mA}$		25		nm
Radiant flux ⁽³⁾⁽⁴⁾	Po	H15	$I_f=350\text{mA}$	255		295	mW
		H16		295		340	

Note:

- (1) ESD protection during chip handling is recommended.
- (2) Basically, the wavelength span is 10nm; however, customers' special requirements are also welcome.
- (3) Radiant flux is determined by using a Au-plated TO-can header without an encapsulant.
- (4) Radiant flux measurement allows a tolerance of $\pm 15\%$.

□ Absolute Maximum Ratings:

Parameter	Symbol	Condition	Rating	Unit
Forward DC current	I_f	$T_a=25^\circ C$	≤ 700	mA
Reverse voltage	V_r	$T_a=25^\circ C$	≤ 5	V
Junction temperature	T_j	---	≤ 115	$^\circ C$
Storage temperature	T_{stg}	chip	-40 ~ +85	$^\circ C$
		chip-on-tape/storage	0 ~ 40	$^\circ C$
		chip-on-tape/transportation	-20 ~ +65	$^\circ C$
Temperature during packaging	---	---	280(<10sec)	$^\circ C$

Note:

Maximum ratings are package dependent. The above maximum ratings were determined using a Metal Core Printed Circuit Board (MCPCB) without an encapsulant. Stresses in excess of the absolute maximum ratings such as forward current and junction temperature may cause damage to the LED.

□ Characteristic Curves:

Fig.1-Relative Luminous Intensity vs. Forward Current

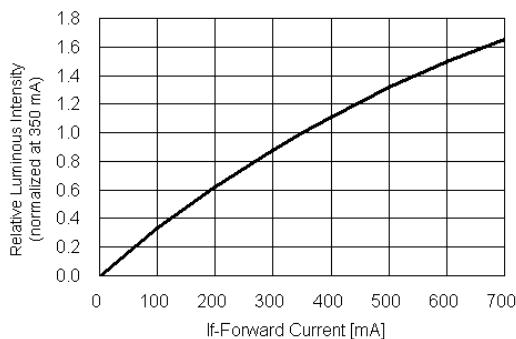


Fig.2- Forward Current vs. Forward Voltage

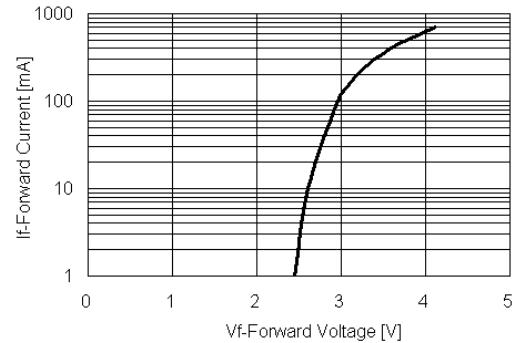


Fig.3-Relative Intensity (@350mA) vs. Ambient Temperature

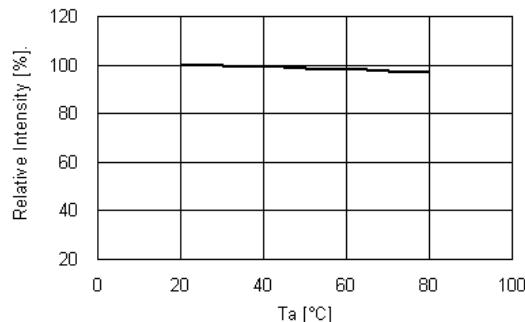


Fig.4-Forward Voltage (@350mA) vs. Ambient Temperature

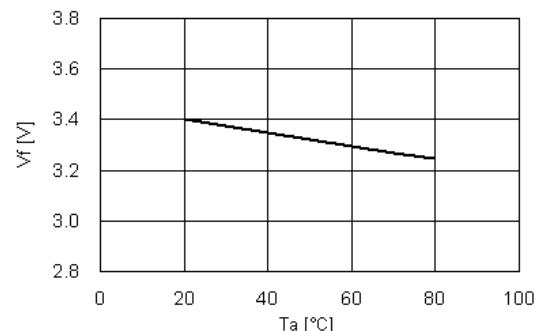


Fig.5-Dominant Wavelength(@350mA) vs. Ambient Temperature

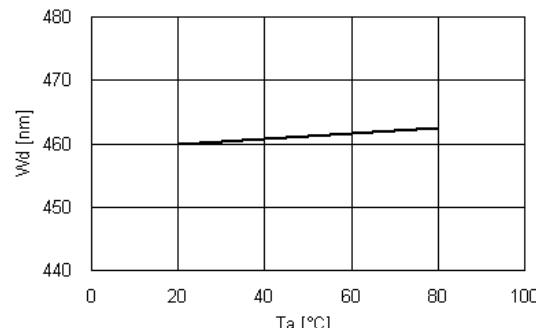


Fig.6 Maximum Driving Forward DC Current vs. Ambient Temperature (Derating based on T_j max. = $115^\circ C$)

